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METHOD FOR SELECTIVE REMOVAL OF UNREACTED METAL AFTER SILICIDATION

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Abstract

A method to remove a metal from over a substrate in the fabrication of an integrated circuit device. The invention comprises providing a metal layer over a substrate. The metal layer is exposed to a reactant gas to form at least a solid metal containing product. The reactant gas preferably contains sulfur and oxygen. The reactant gas more preferably comprises sulfur dioxide or sulfur trioxide. The reactant gas is preferably heated and optionally exposed to a plasma. Next, the metal containing product is removed using a liquid, thereby removing at least portion of the metal layer from over the substrate.

FIGURE 4